# SHANGHAI SUNRISE ELECTRONICS CO., LTD.

## 1N5400G THRU 1N5408G GLASS PASSIVATED

JUNCTION RECTIFIER

TECHNICAL SPECIFICATION

# VOLTAGE: 50 TO 1000V CURRENT: 3.0A

#### FEATURES

- Molded case feature for auto insertion
- Glass passivated chip
- High current capability
- Low leakage current
- High surge capability
- High temperature soldering guaranteed: 250°C/10sec/0.375"(9.5mm) lead length at 5 lbs tension

## **MECHANICAL DATA**

- Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O recognized flame retardant epoxy
- Polarity: Color band denotes cathode
- Mounting position: Any

# MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	1N54 00G	1N54 01G	1N54 02G	1N54 04G	1N54 06G	1N54 07G	1N54 08G	UNITS
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current (9.5mm lead length, at T <sub>L</sub> =105°C)	I <sub>F(AV)</sub>	3.0							А
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I <sub>FSM</sub>	200						А	
Maximum Instantaneous Forward Voltage (at rated forward current)	V <sub>F</sub>	1.0						V	
Maximum DC Reverse Current $T_a=25^{\circ}C$	1	5.0							μA
(at rated DC blocking voltage) T <sub>a</sub> =100°C	I <sub>R</sub>	300							μA
Typical Junction Capacitance (Note 1)	CJ	40							рF
Typical Thermal Resistance (Note 2)	R <sub>θ</sub> (ja)	30							°C/W
Storage and Operation Junction Temperature	$T_{STG}, T_{J}$	-65 to +150						°C	
Note: 1.Measured at 1.0 MHz and applied voltag	ge of 4.0V <sub>d</sub>	0							

2.Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C. board mounted

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